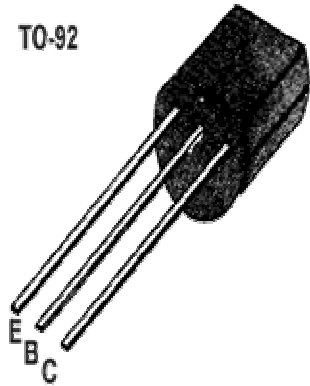


■■ APPLICATION: AMPLIFIER APPLICATION,
SWITCHING APPLICATION.

■■ MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CB0}	-80	V
Collector-emitter voltage	V _{CE0}	-80	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	I _c	-1	A
Collector Power Dissipation	P _c	800	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	- 55~150	°C



■■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h _{FE}	100		300		V _{CE} = -3V, I _c = -100mA
Collector Cut-off Current	I _{CB0}			-0.1	μA	V _{CB} = -80V, I _E =0
Emitter Cut-off Current	I _{EBO}			-0.1	μA	V _{EB} = -5V, I _c =0
Collector-Base Breakdown Voltage	BV _{CB0}	-80			V	I _c = -0.1mA, I _E =0
Collector-Emitter Breakdown Voltage	BV _{CE0}	-80			V	I _c = -1mA, I _B =0
Emitter-Base Breakdown Voltage	BV _{EBO}	-5			V	I _E = -0.1mA, I _c =0
Collector-Emitter Saturation Voltage	V _{CE(sat)}			-0.4	V	I _c = -500mA, I _B = -50mA
Gain bandwidth product	f _T		100		MHz	I _c = -50mA, V _{CE} = -10V
Common Base Output Capacitance	C _{ob}			30	PF	V _{CB} = -10V, I _E =0, f = 1MHz

■■ h_{FE} Classification

Classification

h_{FE} 100~300